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SIDDHARTH INSTITUTE OF ENGINEERING & TECHNOLOGY:: PUTTUR
(AUTONOMOUS)

B.Tech IV Year I Semester Supplementary Examinations November-2020

VLSI DESIGN

(Electronics & Communication Engineering)

Time: 3 hours

Max. Marks: 60

(Answer all Five Units 5 x 12 = 60 Marks)

UNIT-I

1 a With neat diagrams, explain the different steps in n-well fabrication of CMOS transistor. **7M**

b State why NMOS technology is preferred more than PMOS technology. **5M**

OR

2 a With neat diagrams, discuss nMOS fabrication process steps. **6M**

b Mention the differences between CMOS and BiCMOS technologies. **6M**

UNIT-II

3 a Explain design rules for wires and MOS transistors. **6M**

b Explain how the p-MOS transistor forms in lambda-based design rules. **6M**

OR

4 a Draw the stick diagram for the following using CMOS logic. **6M**
(i) $Y=(A+B+C)^1$ (ii) 2-input Nand gate

b Discuss the different contact cuts with an example to each. **6M**

UNIT-III

5 a Write short notes on **6M**
(i) Domino CMOS logic.

(ii) Floor planning.

b Explain in detail about DCV logic. **6M**

OR

6 a Explain **6M**
(i) Power delay estimation.

(ii) Pass transistors and transmission gate.

b Explain how the clock and power distributions employed in VLSI design circuits with diagrams. **6M**

UNIT-IV

7 a List the advantages of Zero/one detector. **5M**

b Draw and explain the shifter implemented by using full adder. **7M**

OR

8 a Write a architecture for a 4- bit Counter in sub circuit design. **6M**

b Explain the 6 transistor Static memory cell. **6M**

UNIT-V

9 a Discuss the merits of FPGA over other architectures. **6M**

b Explain the stuck at 1 and stuck 0 faults with suitable diagrams. **6M**

OR

10 a What is the need for testing? Explain about Fault simulation. **6M**

b Discuss in details about CPLD structure and explain each block. **6M**

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